SILICON EPITAXIAL PLANAR DIODE

Features

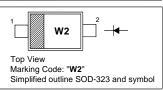
- Low forward voltage
- Fast Reverse Recovery Time
- Small Total Capacitance

Application

• Ultra high speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



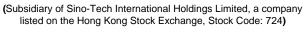
Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Maximum (Peak) Reverse Voltage	V_{RM}	85	V
Reverse Voltage	V_R	80	V
Average Forward Current	Io	100	mA
Maximum (Peak) Forward Current	I _{FM}	200	mA
Surge Forward Current (10 ms)	I _{FSM}	1	А
Power Dissipation	P _{tot}	200	mW
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	1.2	V
Reverse Current at $V_R = 30 \text{ V}$ at $V_R = 80 \text{ V}$	I _R	0.1 0.5	μΑ
Total Capacitance at f = 1 MHz	Ст	3	pF
Reverse Recovery Time at I _F = 10 mA	t _{rr}	4	ns







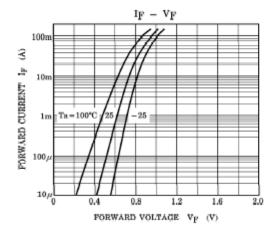


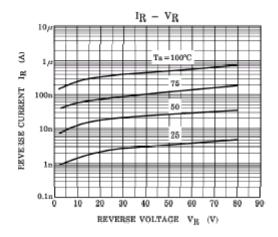


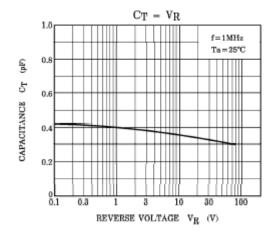




Dated: 07/04/2009















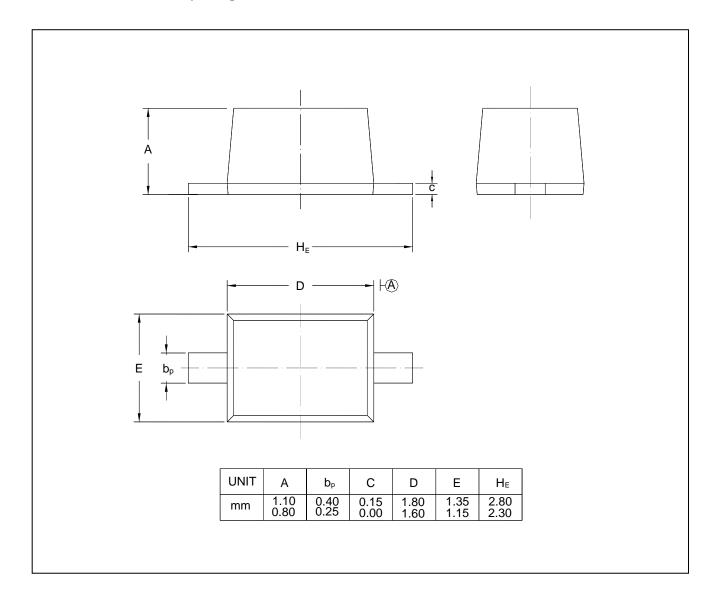




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



SEMTECH ELECTRONICS LTD.









